



500.42877X00

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: N. ISHITSUKA, et al.
Serial No.: 10/600,771
Filed: June 23, 2003
For: SEMICONDUCTOR DEVICE AND MANUFACTURING
METHOD OF THE SAME
Group: 2812
Examiner: H. Jey Tsai
Confirm. No.: 5732

INFORMATION DISCLOSURE STATEMENT
UNDER 37 CFR §1.97 & §1.98

MS: AMENDMENTS

Commissioner For Patents
POB 1450
Alexandria, VA 22313-1450

November 2, 2005

Sir:

In the matter of the above-identified application, applicants, through there undersigned representative, are submitting herewith copies of the two (2) cited art documents which were listed in a recent Office Action in a counterpart foreign (Korean) application and a listing therefor of the same in the attached Form PTO/SB/08A for the USPTO's consideration. The copies of the cited art documents in connection include a U.S. patent and a Korean patent publication (including a Japanese language abstract thereof). A copy of the Korean Office Action along with an available English translation thereof are also enclosed.

This Information Disclosure Statement (IDS) is being submitted prior to the mailing of either a final action on the merits or an official Notice of

Allowance, and, accordingly, is in compliance with 37 CFR §1.97(c).

The following statement as specified under 37 CFR §1.97(e)(1) is being made:

On information and belief, the undersigned submits that each item of information contained in this Information Disclosure Statement (IDS) was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three (3) months prior to the filing of this IDS.

To the extent that listed Korean Patent Publication No. 1998-015456 is not in the English language, the requirement of 37 C.F.R. §1.98(a)(3) for a concise explanation of the relevance thereof is satisfied by:

The submission of an available English language version of the Korean Office Action as well as by the discussion related thereto, based on that provided by applicants to the undersigned representative, which is summarized hereinbelow.

Regarding Korean Patent Publication No. 1998-015456, it is observed that in Fig. 6 thereof the height of the insulation film that is deposited on the element isolation groove 12 reaches the surface of the substrate 10. Numeral 13 in Fig. 6 thereof denotes the gate oxide film 13. It is apparent therefore that the height reached by the insulation film deposited on the element isolation groove 12 is higher than that of the source and drain.

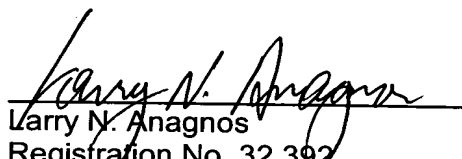
The following comments were also provided by applicants regarding the listed U.S. Patent No. 6,243,286. With regard to the embodiment illustrated in Fig. 18 thereof, it is observed that the referred to field oxide film 13 relates to

what applicants call as a "LOCOS" structure. In this regard it is noted that the field oxide film 13 is remarkably different from that of the element isolation groove. Even if one would attempt to consider the field oxide film 13 as being equivalent to an element isolation groove, the fact still remains that the height achieved by the insulating film of the field oxide region 13 is higher than that of the positions of both the source and the drain, which is, applicants submit, quite different from that of the present invention.

It is submitted this IDS is in compliance with the rules of practice as well as with USPTO guidelines. Therefore, applicants respectfully request that it be entered and duly considered by the USPTO. Also, acknowledgment of entry as well as of formal consideration thereof by the Examiner is respectfully requested.

If any costs are due in accordance with the filing of this Information Disclosure Statement, please charge same to the account of Antonelli, Terry, Stout & Kraus, LLP, Account No. 01-2135 (500.42877X00).

Respectfully submitted,
ANTONELLI, TERRY, STOUT & KRAUS, LLP


Larry N. Anagnos
Registration No. 32,392

LNA/gjb
(703) 312-6600

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Complete if Known	
				Application Number	10/600,771
				Filing Date	June 23, 2003
				First Named Inventor	N. ISHITSUKA, et al.
				Art Unit	2812
				Examiner Name	H. Jey Tsai
				Attorney Docket Number	500.42877X00
Sheet 1 of 1					

[illegible][illegible]

Examiner Signature		Date Considered	
-----------------------	--	--------------------	--

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Applicant's unique citation designation number (optional). ²See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³Enter Office that issued the document, by the two-letter code (WIPO Standard St.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to place a check mark here if English language Translation is attached.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, DC 20231. **DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO:** Assistant Commissioner for Patents, Washington, DC 20231.